EE4C10 Analog Circuit Design Fundamentals

Homework Assignment I

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Problem 1

For $I_D = 40 \mu A$:

$$I_D = \frac{1.8V - V_D}{R}$$

$$V_D = 1.8V - I_D R$$

$$V_D = 1.0V$$

Saturation region:

$$V_{GS} = 1.0V > V_{TH}$$

$$V_{GS} - V_{TH} = 0.4V < V_{DS}$$

1.
$$\lambda = 0V^{-1}$$

$$I_{D} = \frac{\mu_{n}C_{OX}}{2} \frac{W}{L} (V_{GS} - V_{TH})^{2}$$

$$L = \frac{\mu_{n}C_{OX}}{2} \frac{W}{I_{D}} (V_{GS} - V_{TH})^{2}$$

$$L = 0.39 \mu m$$

2.
$$\lambda = 0.06V^{-1}$$

$$I_{D} = \frac{\mu_{n} C_{OX}}{2} \frac{W}{L} (V_{GS} - V_{TH})^{2} (1 + \lambda V_{DS})$$

$$L = \frac{\mu_{n} C_{OX}}{2} \frac{W}{I_{D}} (V_{GS} - V_{TH})^{2} (1 + \lambda V_{DS})$$

$$\underline{L} = 0.41 \mu m$$

Problem 2

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$

1. Bulk of the transistors are connected to the source, $V_B = V_S$

$$V_{TH} = V_{TH0} + \gamma(\sqrt{2\varphi_F + V_{BS}} - \sqrt{|2\varphi_F|})$$

$$V_{TH} = V_{TH0} = 0.33V$$

(a) Transistor M₁

$$V_{SG} = 2.5V - 1.7V = 0.8V$$

$$I_D = \frac{\mu_p C_{OX}}{2} \frac{W}{L} (V_{SG} - V_{TH})^2$$

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$

$$W_1 = 2.72 \mu m$$

(b) Transistor M₂

$$V_{SG} = 1.7V - 1V = 0.7V$$

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$
$$W_2 = 4.38 \mu m$$

(c) Transistor M₃

$$V_{SG} = 1V$$

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$

$$W_3 = 1.37 \mu m$$

- 2. Bulk terminals are attached to the V_{DD} , $V_B = V_{DD}$.
 - (a) Transistor M₁

$$V_{BS} = 2.5V - 2.5V = 0V$$

$$V_{TH} = V_{TH0} + \gamma(\sqrt{2\varphi_F + V_{BS}} - \sqrt{|2\varphi_F|})$$

$$V_{TH} = V_{TH0} = 0.33V$$

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$

$$W_1 = 2.72 \mu m$$

(b) Transistor M₂

$$V_{BS} = 2.5V - 1.7V = 0.8V$$

$$V_{TH} = V_{TH0} + \gamma(\sqrt{2\varphi_F + V_{BS}} - \sqrt{|2\varphi_F|})$$

$$V_{TH} = V_{TH0} = 0.43V$$

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$

$$W_2 = 8.23 \mu m$$

(c) Transistor M₃

$$V_{BS} = 2.5V - 1.0V = 1.5V$$

$$\begin{split} V_{TH} &= V_{TH0} + \gamma (\sqrt{2\varphi_F + V_{BS}} - \sqrt{|2\varphi_F|}) \\ V_{TH} &= V_{TH0} = 0.49V \end{split}$$

$$W = \frac{2LI_D}{\mu_p C_{OX}} \frac{1}{(V_{SG} - V_{TH})^2}$$

$$W_3 = 2.31 \mu m$$

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